

Growth Rates During Silicon Spatial Electron-Enhanced Atomic Layer Deposition: Role of Dangling Bond Lifetimes

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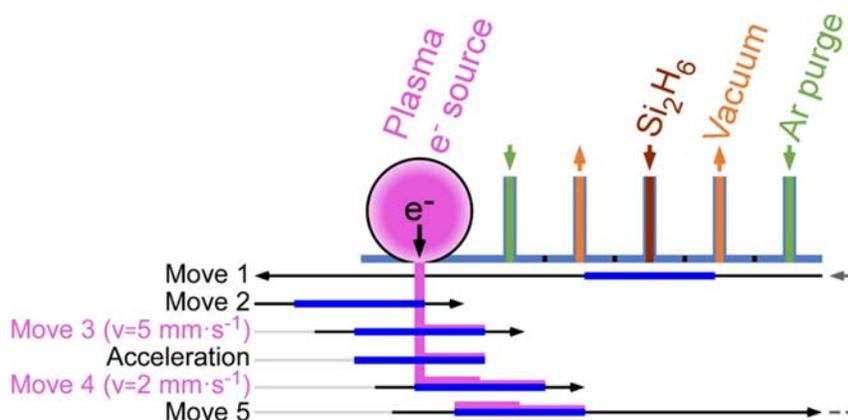


Figure S1. Schematic of movement of 6" wafer in spatial ALD reactor showing the positions of the electron source and the Si₂H₆ precursor. The wafer can move at different velocities under the electron source to vary the electron dose.

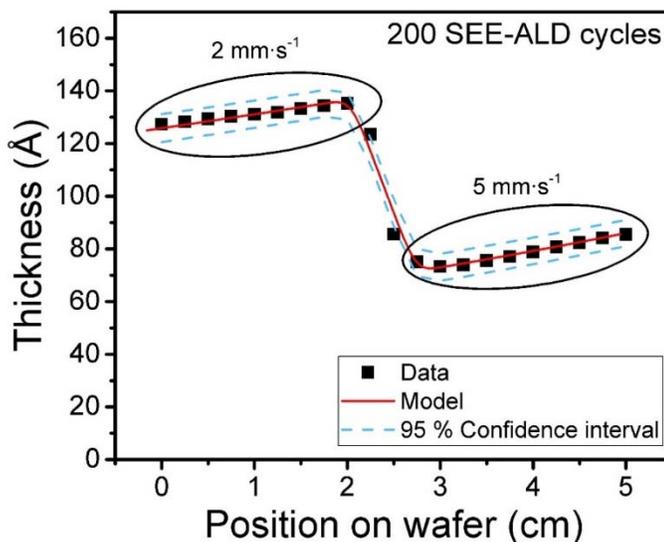


Figure S2. Silicon thickness measured on the 6" wafer after 200 SEE-ALD cycles for two different wafer velocities under the electron source to vary the electron dose.